

BUK9Y8R5-80E

N-channel 80 V, 8.5 m Ω logic level MOSFET in LFPAK56 Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	238	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	6.3	8.5	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 64 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	17.1	-	nC

^[1] Continuous current is limited by package.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source		
3	S	source	q	G T T
4	G	gate	وققق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y8R5-80E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y8R5-80E	98E580

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>	[3]	-	100	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>	[3]	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	423	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	238	W

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode		'			
I _S	source current	T _{mb} = 25 °C	[3]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	423	Α
Avalanche ru	uggedness		'			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[4][5]	-	148	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_j$ and or $\rm V_{GS}$
- [2]
- Continuous current is limited by package. [3]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information. [4]

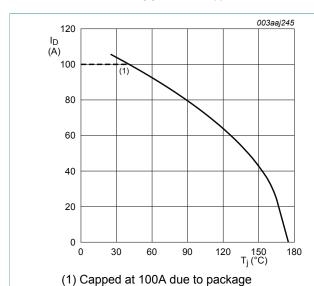


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

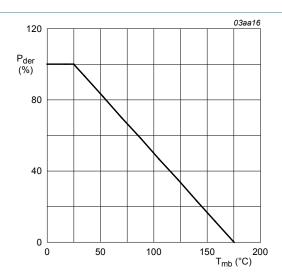


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

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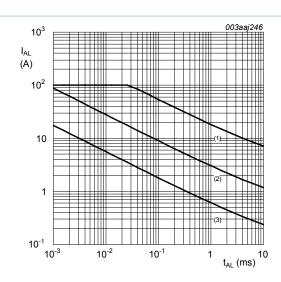


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j \ (init)} = 25 \,^{\circ}C$; (2) $T_{j \ (init)} = 150 \,^{\circ}C$; (3) Repetitive Avalanche

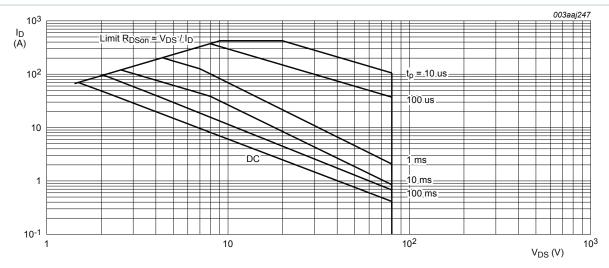


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

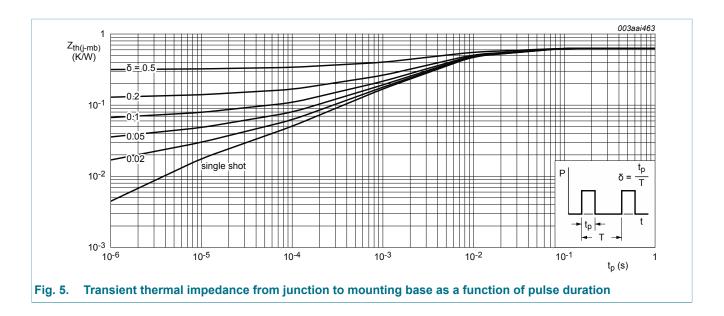
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.63	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				'	
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.07	10	μA
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	6.3	8.5	mΩ
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	5.8	8	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	21.3	mΩ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{Fig. 13}; \text{Fig. 14}$	-	54.7	-	nC
Q _{GS}	gate-source charge		-	13.5	-	nC
Q_{GD}	gate-drain charge		-	17.1	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	6125	8167	pF
C _{oss}	output capacitance		-	397	476	pF
C _{rss}	reverse transfer capacitance		-	207	284	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 60 \text{ V}; R_L = 2.4 \Omega; V_{GS} = 5 \text{ V};$	-	28	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	50	-	ns
t _{d(off)}	turn-off delay time		-	82	-	ns
t _f	fall time		-	45	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	30.9	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	36.3	-	nC

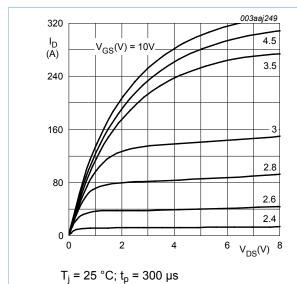


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

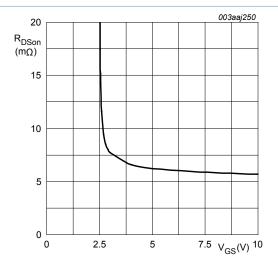


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

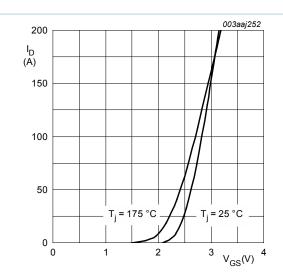


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



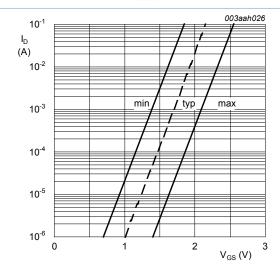


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

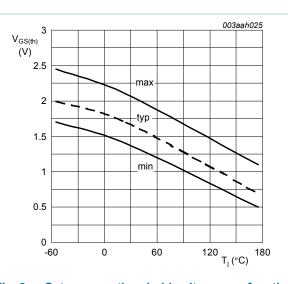
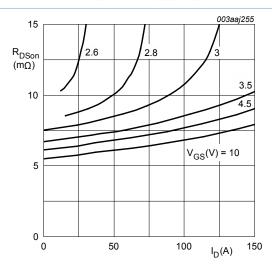


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 T_i = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

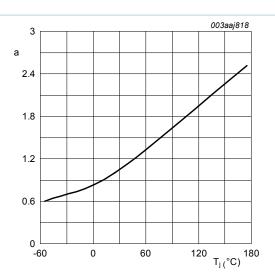


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

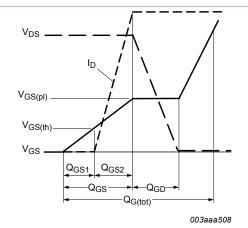


Fig. 14. Gate charge waveform definitions

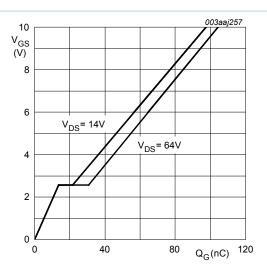


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 25$ A

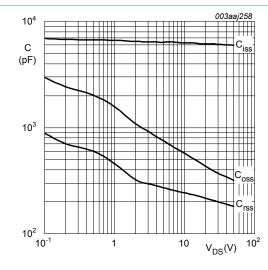


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

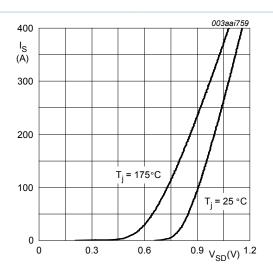
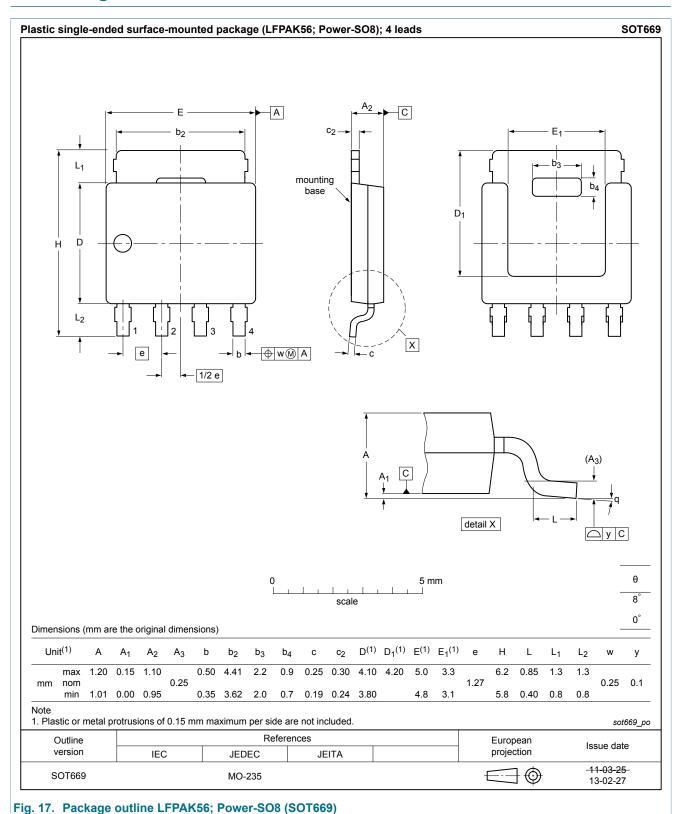


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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